

## SIPMOS® Power-Transistor

### Feature

- N-Channel
- Enhancement mode
- 175°C operating temperature
- Avalanche rated
- dv/dt rated

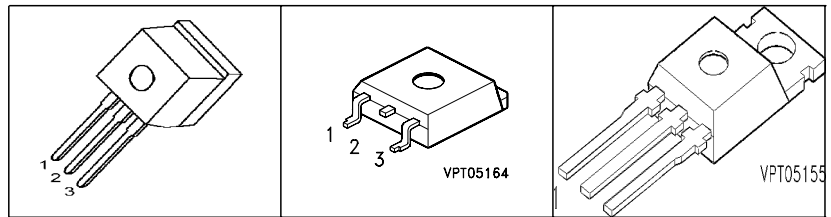
### Product Summary

$V_{DS}$	100	V
$R_{DS(on)}$	33	m $\Omega$
$I_D$	47	A

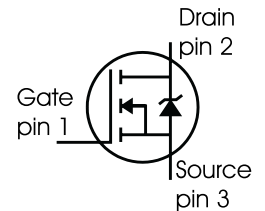
P-TO262-3-1

P-TO263-3-2

P-TO220-3-1



Type	Package	Ordering Code	Marking
SPP47N10	P-TO220-3-1	Q67040-S4183	47N10
SPB47N10	P-TO263-3-2	Q67040-S4173	47N10
SPI47N10	P-TO262-3-1	Q67060-S7431	47N10



### Maximum Ratings, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	$I_D$	47	A
$T_C=25^\circ\text{C}$		47	
$T_C=100^\circ\text{C}$		33	
Pulsed drain current	$I_D \text{ puls}$	188	
$T_C=25^\circ\text{C}$			
Avalanche energy, single pulse	$E_{AS}$	400	mJ
$I_D=47\text{ A}$ , $V_{DD}=25\text{V}$ , $R_{GS}=25\Omega$			
Avalanche energy, periodic limited by $T_{jmax}$	$E_{AR}$	17.5	
Reverse diode dv/dt	dv/dt	6	kV/ $\mu\text{s}$
$I_S=47\text{A}$ , $V_{DS}=0\text{V}$ , $di/dt=200\text{A}/\mu\text{s}$			
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation	$P_{tot}$	175	W
$T_C=25^\circ\text{C}$			
Operating and storage temperature	$T_j, T_{stg}$	-55... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/175/56	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.85	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>1)</sup>	$R_{thJA}$	-	-	62 40	

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain-source breakdown voltage $V_{GS}=0V, I_D=2mA$	$V_{(BR)DSS}$	100	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = 2\text{ mA}$	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS}=100V, V_{GS}=0V, T_j=25^\circ\text{C}$ $V_{DS}=100V, V_{GS}=0V, T_j=150^\circ\text{C}$	$I_{DSS}$	-	0.1	1 100	$\mu\text{A}$
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	$I_{GSS}$	-	10	100	
Drain-source on-state resistance $V_{GS}=10V, I_D=33A$	$R_{DS(on)}$	-	25	33	$\text{m}\Omega$

<sup>1</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

### Dynamic Characteristics

Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 33A$	13	26	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V,$ $f = 1MHz$	-	2000	2500	pF
Output capacitance	$C_{oss}$		-	370	465	
Reverse transfer capacitance	$C_{rss}$		-	190	240	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50V, V_{GS} = 10V,$ $I_D = 47A, R_G = 4.7\Omega$	-	25	39	ns
Rise time	$t_r$		-	23	36	
Turn-off delay time	$t_{d(off)}$		-	63	99	
Fall time	$t_f$		-	15	22.5	

### Gate Charge Characteristics

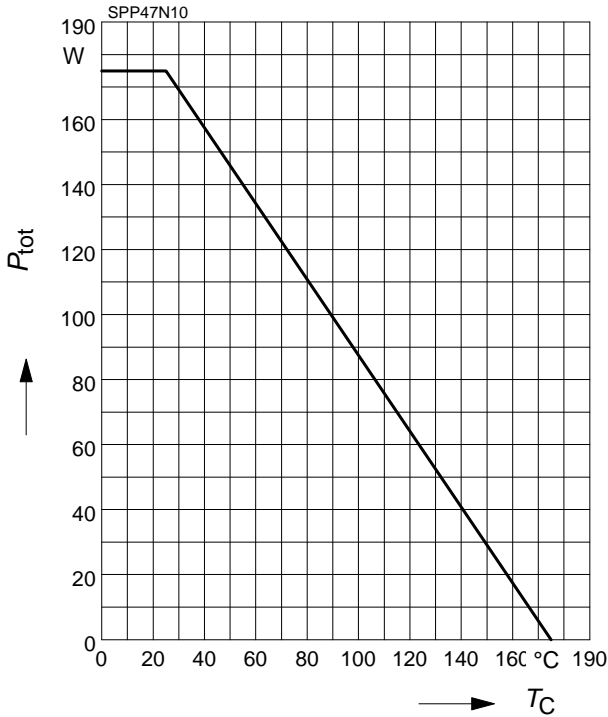
Gate to source charge	$Q_{gs}$	$V_{DD} = 80V, I_D = 47A$	-	19	28.5	nC
Gate to drain charge	$Q_{gd}$		-	29	43.5	
Gate charge total	$Q_g$	$V_{DD} = 80V, I_D = 47A,$ $V_{GS} = 0 \text{ to } 10V$	-	70	105	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 80V, I_D = 47A$	-	6.03	-	V

### Reverse Diode

Inverse diode continuous forward current	$I_S$	$T_C = 25^\circ\text{C}$	-	-	47	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	188	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0V, I_F = 94A$	-	1.1	1.5	V
Reverse recovery time	$t_{rr}$	$V_R = 50V, I_F = I_S,$ $di_F/dt = 100A/\mu s$	-	100	150	ns
Reverse recovery charge	$Q_{rr}$		-	400	600	

### 1 Power dissipation

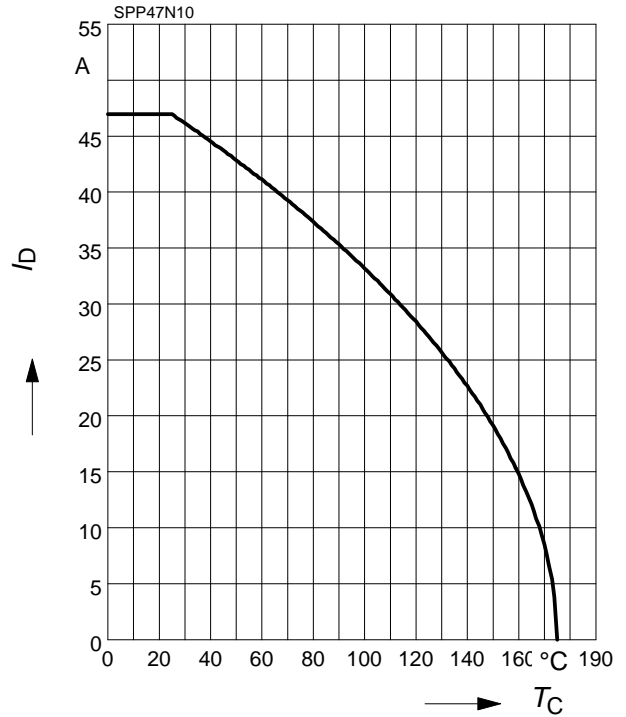
$$P_{tot} = f(T_C)$$



### 2 Drain current

$$I_D = f(T_C)$$

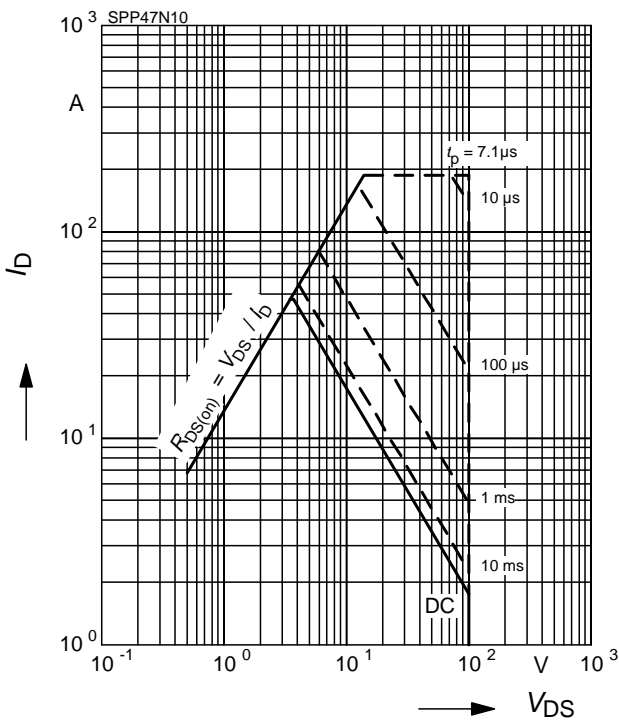
parameter:  $V_{GS} \geq 10\text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

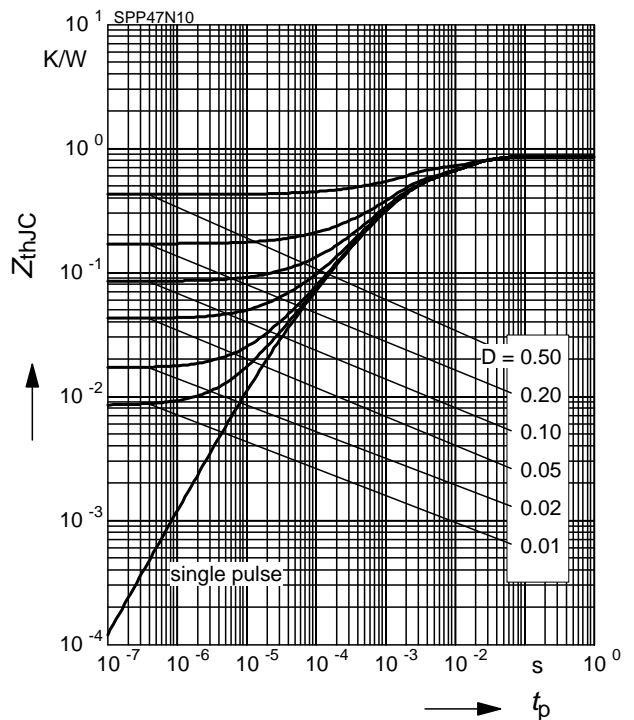
parameter:  $D = 0, T_C = 25\text{ °C}$



### 4 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

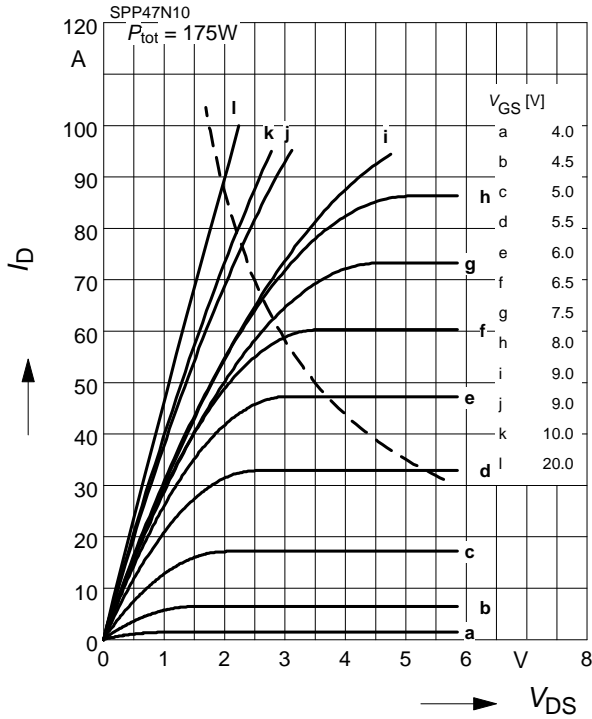
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

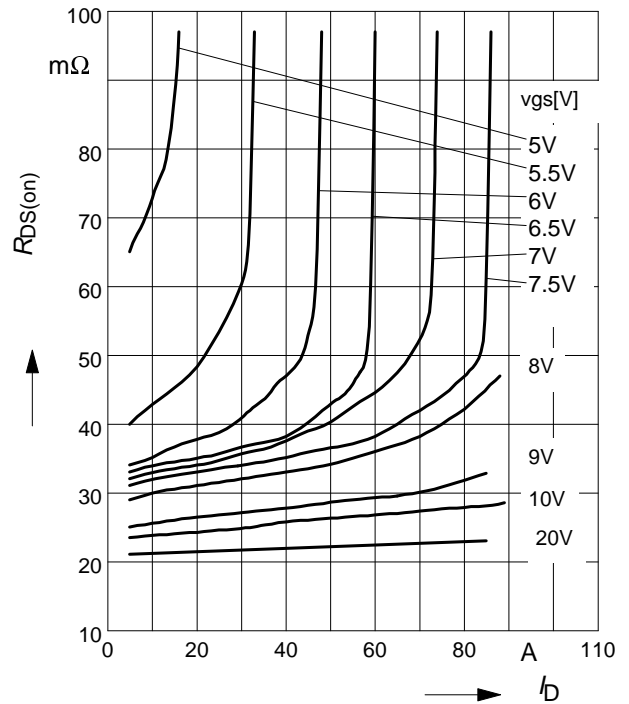
parameter:  $t_p = 80 \mu\text{s}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

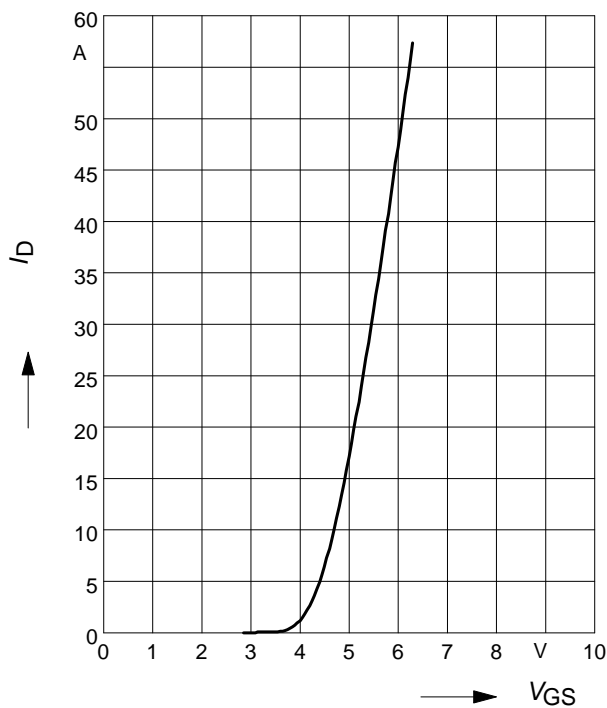
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

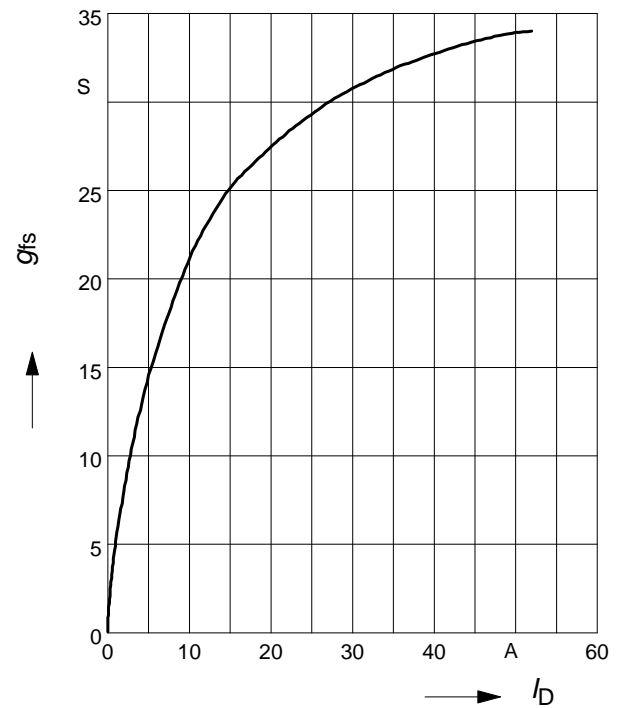
parameter:  $t_p = 80 \mu\text{s}$



**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

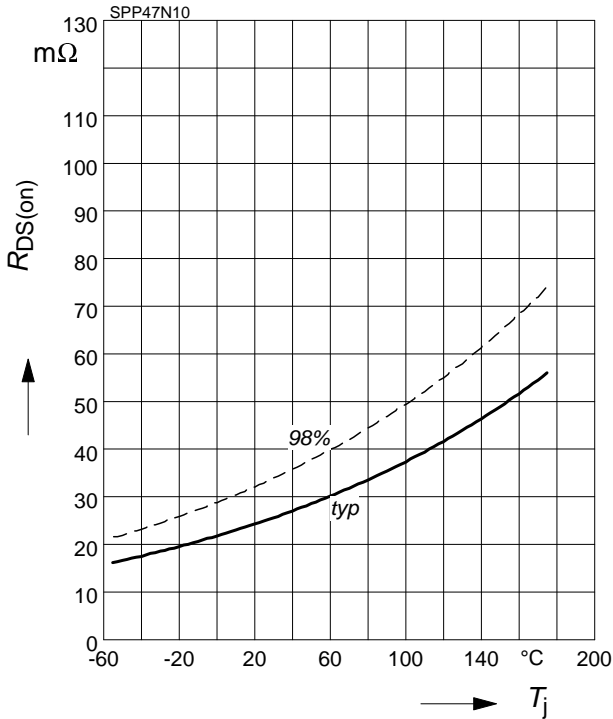
parameter:  $g_{fs}$



### 9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

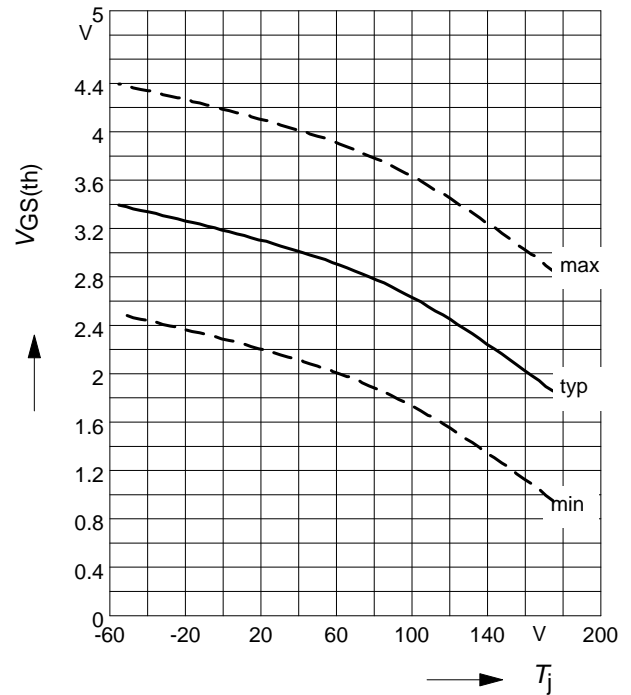
parameter:  $I_D = 33\text{ A}$ ,  $V_{GS} = 10\text{ V}$



### 10 Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

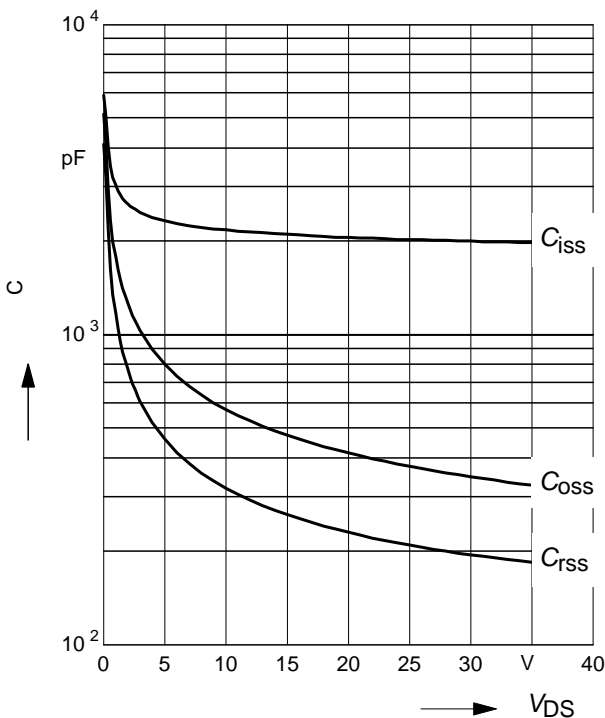
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = 2\text{ mA}$



### 11 Typ. capacitances

$$C = f(V_{DS})$$

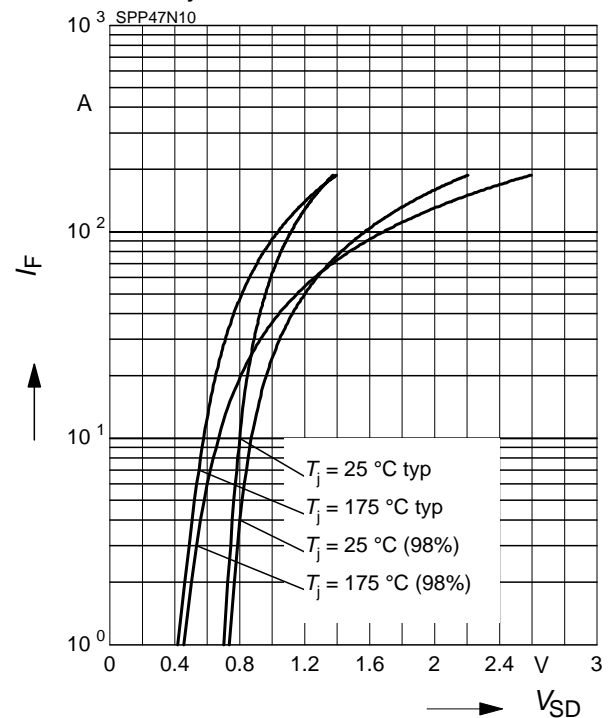
parameter:  $V_{GS} = 0\text{ V}$ ,  $f = 1\text{ MHz}$



### 12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

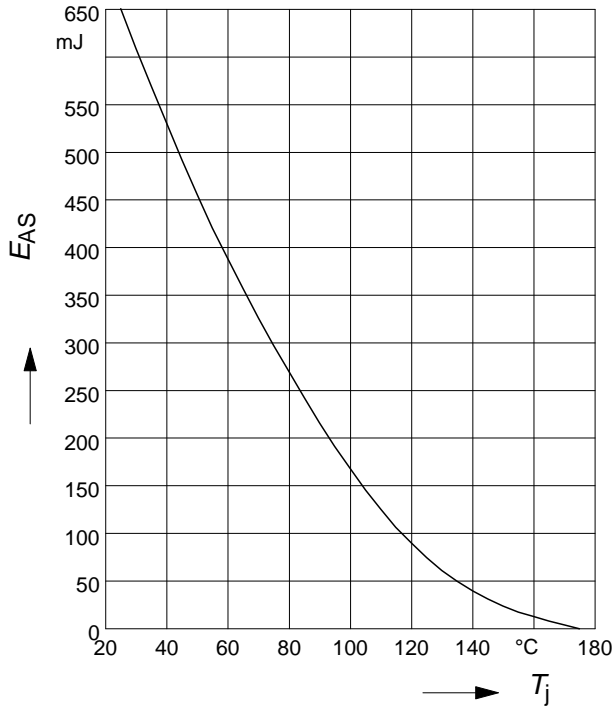
parameter:  $T_j$ ,  $t_p = 80\text{ }\mu\text{s}$



**13 Typ. avalanche energy**

$$E_{AS} = f(T_j)$$

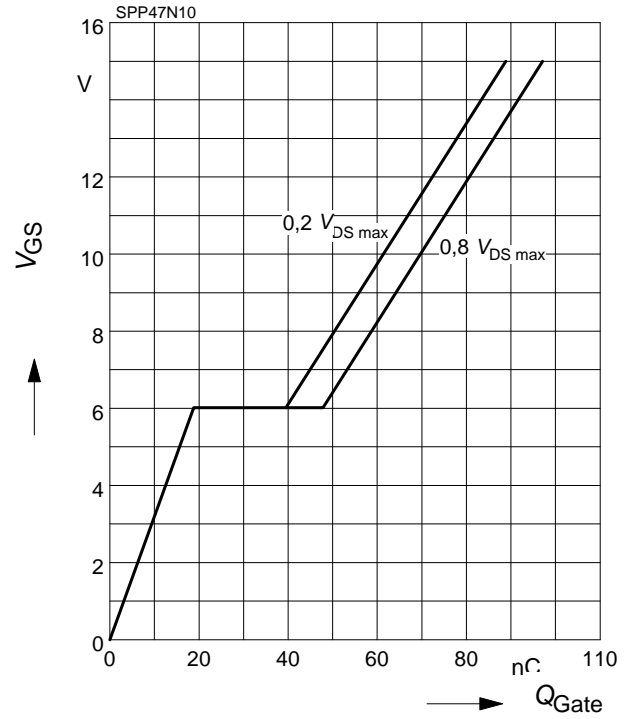
par.:  $I_D = 47 \text{ A}$  ,  $V_{DD} = 25 \text{ V}$ ,  $R_{GS} = 25 \Omega$



**14 Typ. gate charge**

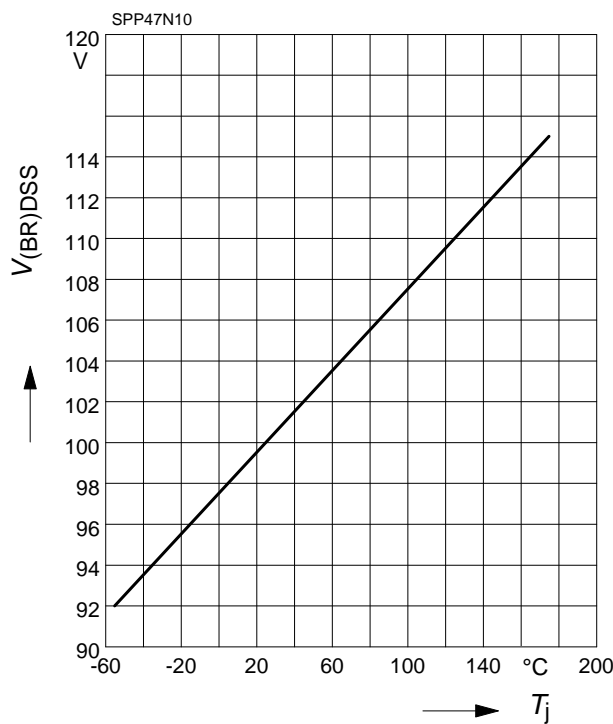
$$V_{GS} = f(Q_{Gate})$$

parameter:  $I_D = 47 \text{ A}$  pulsed



**15 Drain-source breakdown voltage**

$$V_{(BR)DSS} = f(T_j)$$



**Published by**  
**Infineon Technologies AG,**  
**Bereichs Kommunikation**  
**St.-Martin-Strasse 53,**  
**D-81541 München**  
**© Infineon Technologies AG 1999**  
**All Rights Reserved.**

**Attention please!**

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

**Information**

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

**Warnings**

Due to technical requirements components may contain dangerous substances.  
For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

**Further information**

Please notice that the part number is BSPP47N10, BSPB47N10 and BSPI47N10, for simplicity the device is referred to by the term SPP47N10, SPB47N10 and SPI47N10 throughout this documentation